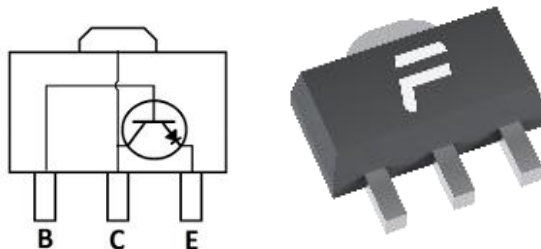


SOT-89-3L Bipolar Transistor 双极型三极管
■ Features 特点

NPN General Purpose 通用


■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	BCX54/ -10/-16	BCX55/ -10/-16	BCX56/ -10/-16	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	45	60	100	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	45	60	80	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	5			V
Collector Current 集电极电流	I_C	1000			mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$	500			mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250			$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$			

■ Device Marking 产品打标

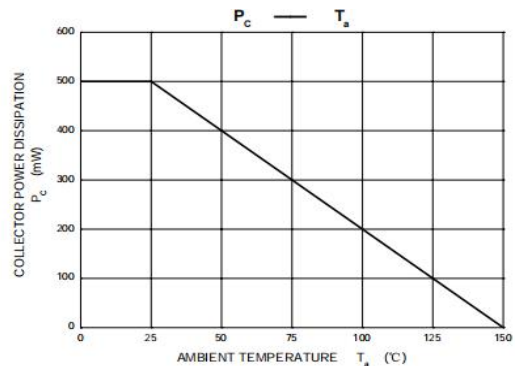
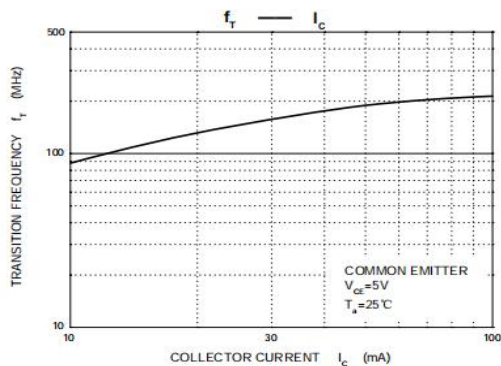
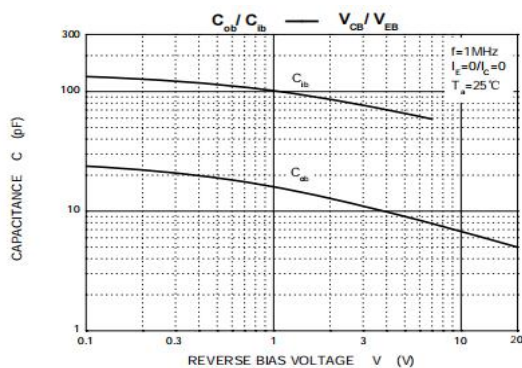
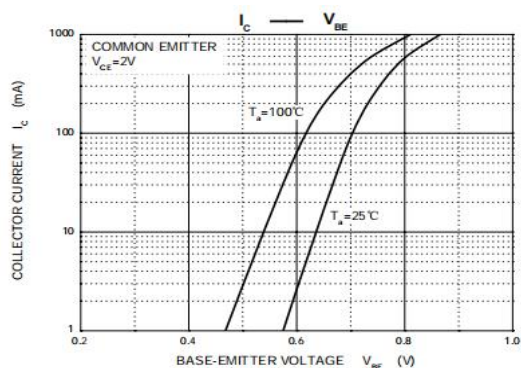
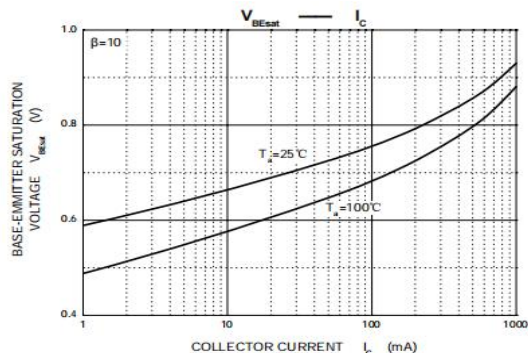
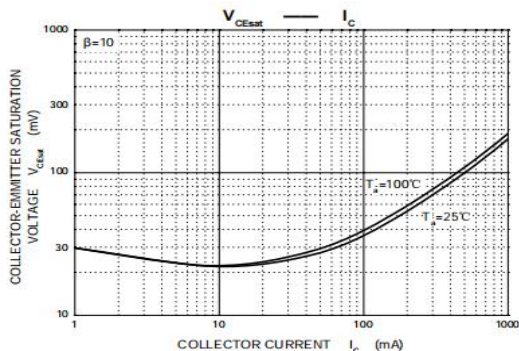
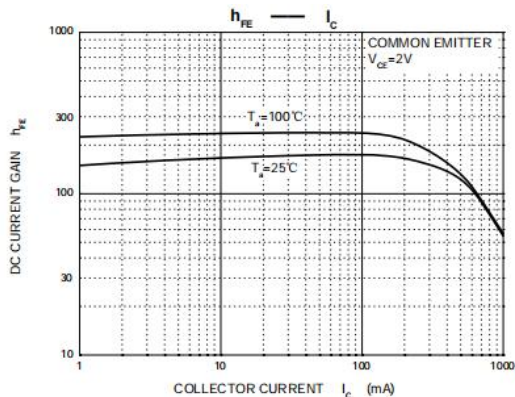
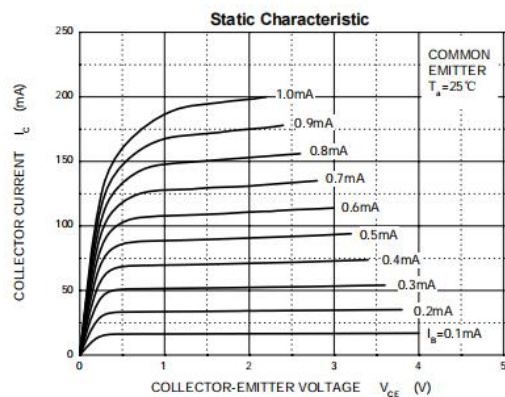
$H_{FE}(2)$		63-250	63-160(-10)	100-250(-16)
Mark	BCX54	BA	BC	BD
	BCX55	BE	BG	BM
	BCX56	BH	BK	BL

■Electrical Characteristics 电特性

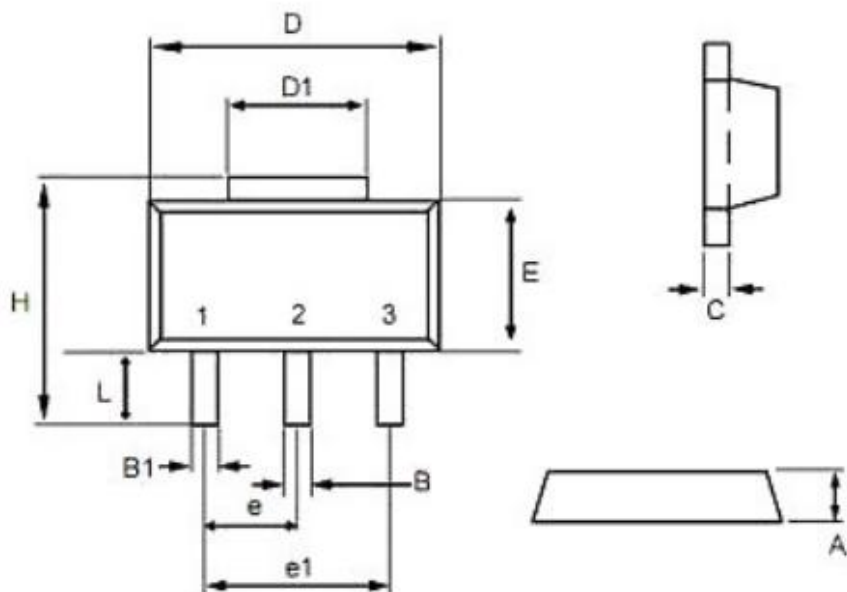
(TA=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数		Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压 (IC= 100uA, IE=0)	BCX54/-10/-16	BV _{CBO}	45	—	—	V
	BCX55/-10/-16		60			
	BCX56/-10/-16		100			
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压 (IC= 10mA, IB=0)	BCX54/-10/-16	BV _{CEO}	45	—	—	V
	BCX55/-10/-16		60			
	BCX56/-10/-16		80			
Emitter-Base Breakdown Voltage 发射极基极击穿电压(IE= 100uA, IC=0)		BV _{EBO}	5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流	BCX54/-10/-16 (V _{CB} = 30V,IE=0)	I _{CBO}	—	—	100	nA
	BCX55/-10/-16 (V _{CB} = 50V,IE=0)					
	BCX56/-10/-16 (V _{CB} = 80V,IE=0)					
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = 5V, IC=0)		I _{EBO}	—	—	100	nA
DC Current Gain 直流电流增益(V _{CE} = 2V,IC= 5mA)		H _{FE} (1)	40	—	—	
DC Current Gain 直流电流增益 (V _{CE} =2V,IC=0.15A)	BCX54/BCX55/BCX56	H _{FE} (2)	63	—	250	
	BCX54/BCX55/BCX56-10		63		160	
	BCX54/BCX55/BCX56-16		100		250	
DC Current Gain 直流电流增益(V _{CE} = 2V,IC= 0.5A)		H _{FE} (3)	25	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(IC= 0.5A, IB= 50mA)		V _{CE(sat)}	—	—	0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(IC= 500mA, IB= 50mA)		V _{BE(sat)}	—	—	1	V
Base-Emitter On Voltage 基极发射极导通电压(V _{CE} = 2V,IC= 0.5A)		V _{BE(on)}	—	—	1	V
Transition Frequency 特征频率(V _{CE} = 5V, IC= 10mA)		f _T	—	130	—	MHz
Output Capacitance 输出电容(V _{CB} = 10V, IE=0, f=1MHz)		C _{ob}	—	15	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047